
CMOS Monolithic Pixels R&D at LBNL

LCWS06 – Linear Collider Workshop 2006

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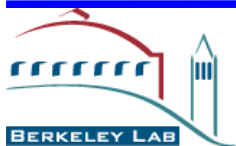
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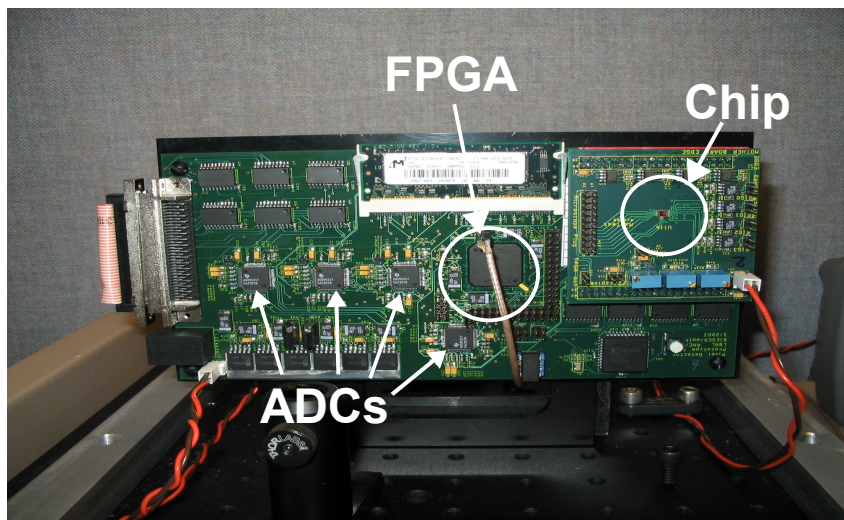
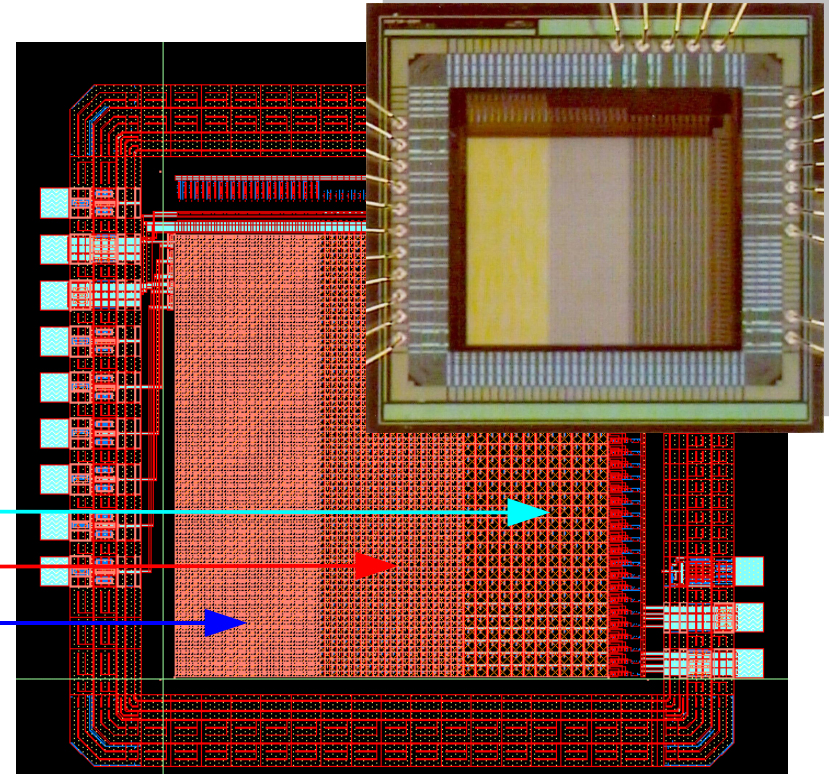
Introduction: Silicon Pixel R&D at LBNL

- ILC Silicon Pixel R&D supported by 3-year Laboratory Directed R&D funding started in October 2004
- R&D directions:
 - sensor design and characterization
 - readout development
 - back-thinning tests
 - pixel module engineering
- Synergy with other on-going LBNL activities on CMOS pixels: STAR VXD upgrade, electron microscopy
- Availability of test facilities on site:
 - Advanced Light Source: beam-tests with 1.5 GeV e^-
 - 88-inch Cyclotron: irradiations with 30-50 MeV p, neutrons
 - National Center for Electron Microscopy (NCEM)



Pixel design and characterization

- **First CMOS pixel test structure** developed and fabricated (through MOSIS) in 2005 in collaboration with LBNL Engineering Division
- **0.35 μm OPTO AMS prototype, 3-T pixels, serial analog readout**
- **Three pixel geometries**
 - **12 x 36 40 μm pixels**
 - **24 x 72 20 μm pixels**
 - **48 x 144 10 μm pixels**

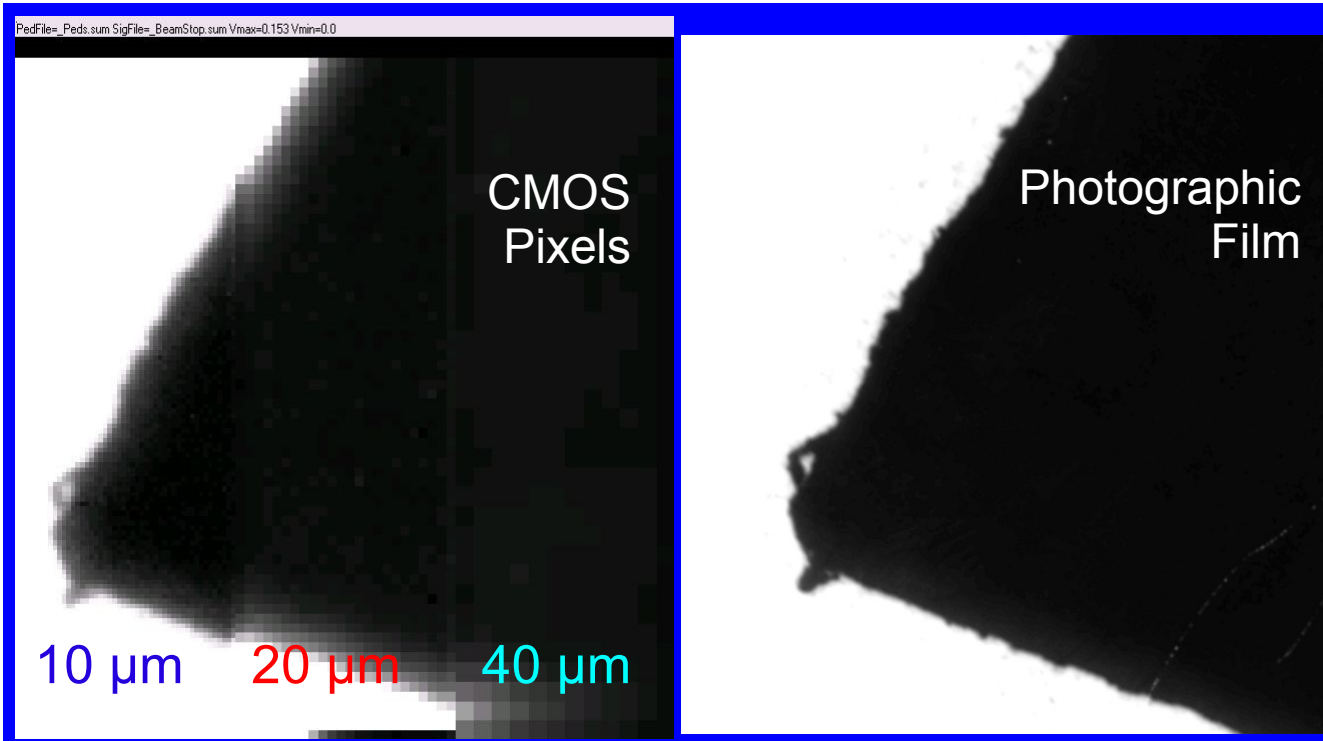


- **Xilinx FPGA based readout board** (LBNL development)
- **14 bit digitization, interface with PC with LabView program for data acquisition and on-line event display**
- **C++/ROOT based off-line data analysis**

Electron Microscope test @ NCEM

- Detector mounted on **Gatan bright field STEM**
- Cycle Reset → 100 ms Integration → Digitization
- 200 images acquired with **~10 primary e⁻ (200 keV)/image**
- **Noise and gain at room T determined from flat field at low intensity**

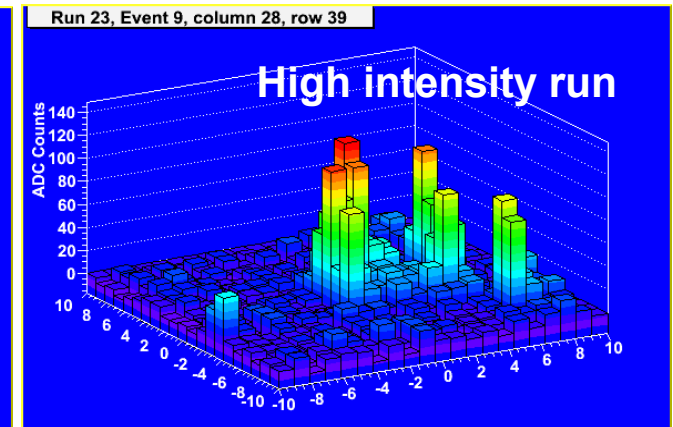
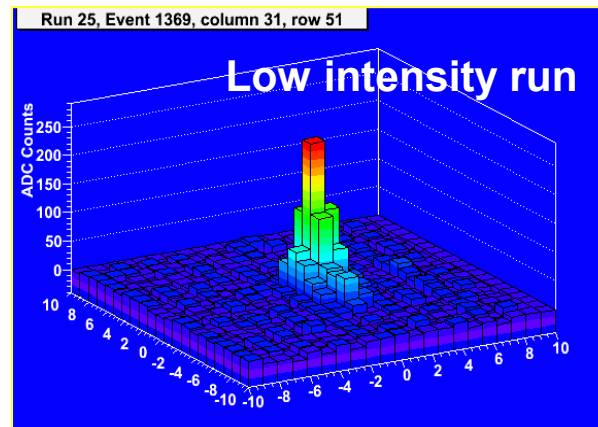
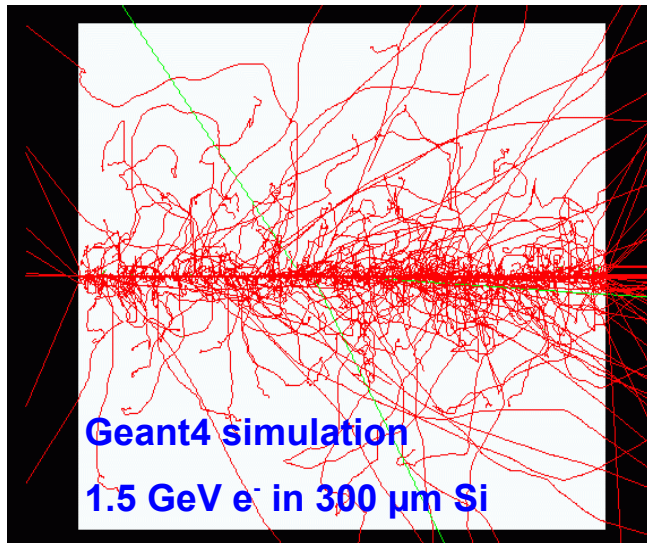
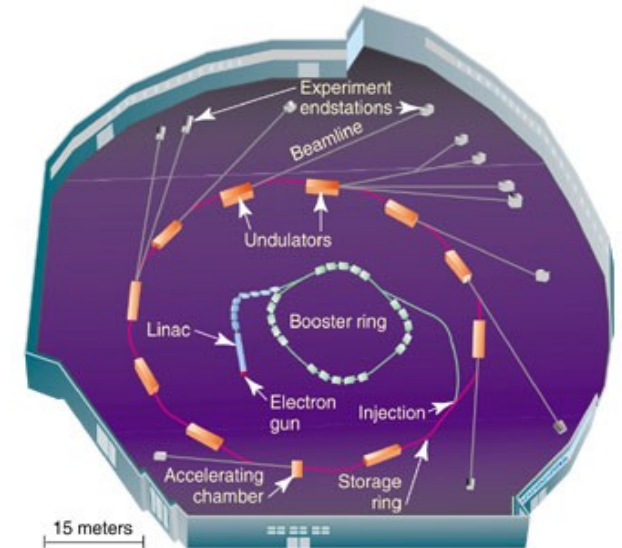
Beam Stop Image with 200 keV e⁻



Pitch (μm)	10	20	40
Noise (mV)	3.0	4.4	6.5
Gain (mV/e ⁻)	25	29	35
Single e ⁻ S/N	8.3	6.6	5.4

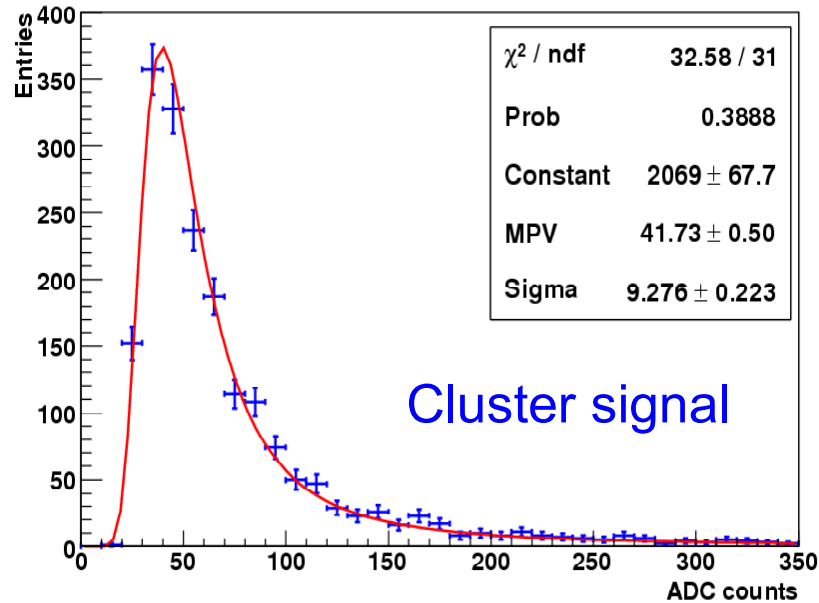
Beam-test at the Advanced Light Source

- Test performed at the BTS beam line of the Advanced Light Source (ALS)
- Single bunch of primary **1.5 GeV e^- @ 1 Hz**, tunable particle flux
- **Readout sequence:**
 - detector kept in reset between 2 bunches
 - trigger on beam pickup signal, read 4 frames
 - timing tuned to record signal on 3rd frame
 - readout with **1 ms integration time**
- Pixel noise and pedestals initialized with beam off, update during run on empty frames

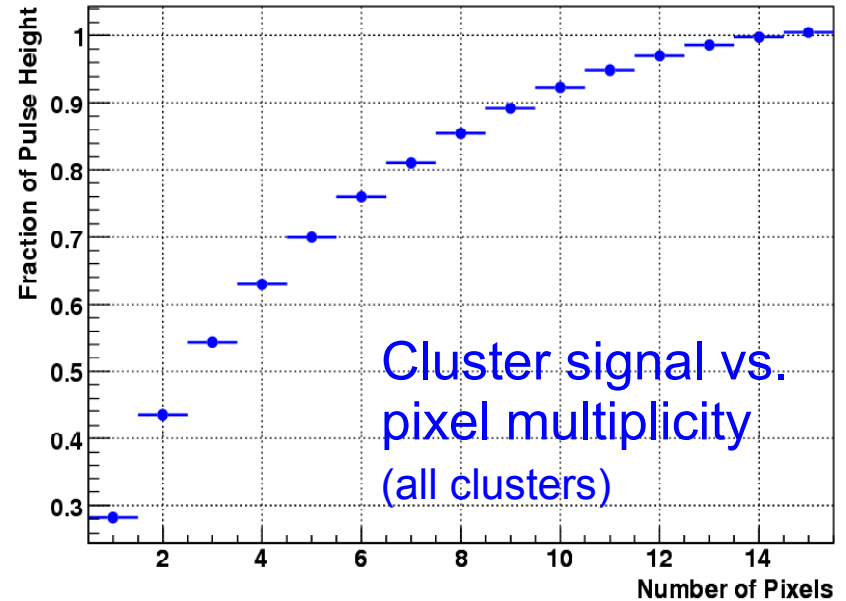


Beam-test results

Cluster pulse height, $10 \times 10 \mu\text{m}^2$



Cluster Pulse Height vs. Number of Pixels



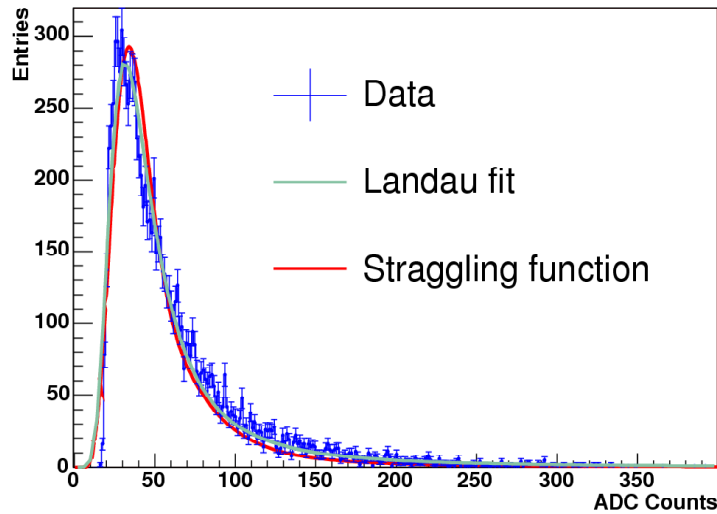
- All measurements performed at **room temperature** (24°C)
- Reconstruct hit clusters from **pulse height-sorted seed pixels** and **neighbors satisfying additional S/N cut**
- Select **isolated and symmetric clusters**

Pixel pitch	10 μm	20 μm	40 μm
<Nb Pixels>	2.71	2.67	2.37
<S/N>	14.1	14.5	15.4

Detector signal studies

Determine sensitive thickness from beam-test data

Cluster Pulse Height

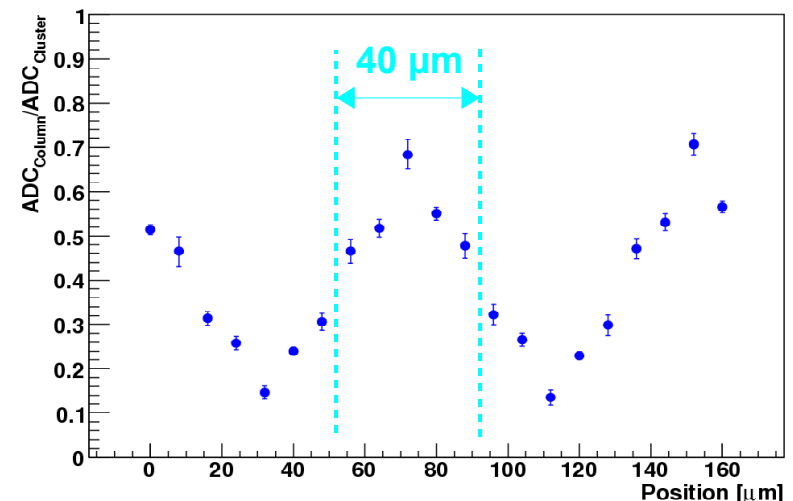


- Hit rate ~50 hits/event at room temperature
- Compare width of Landau fit to e^- data to thin straggling function prediction for different active volume thicknesses
- Best agreement for 10 μm of Si, corresponding to MPV energy loss of 1.86 keV \rightarrow 505 e^-

Determine spatial resolution from laser scan

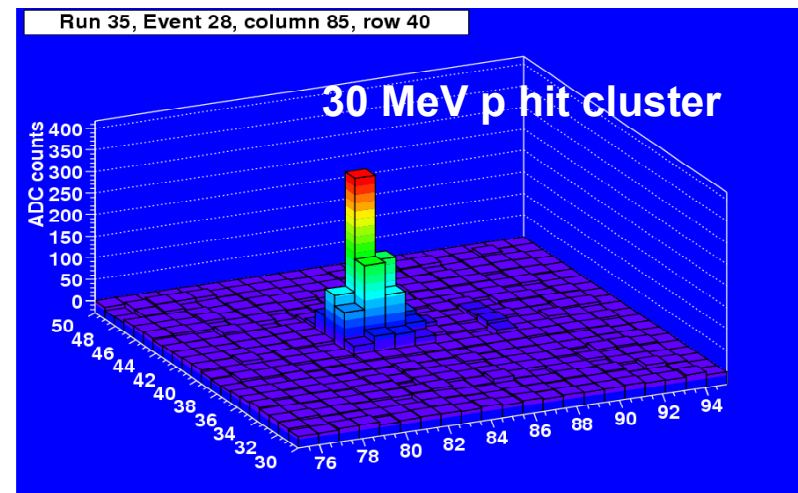
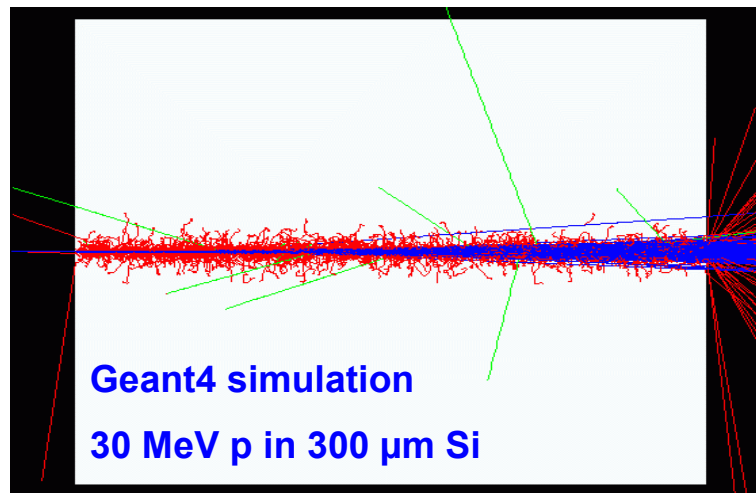
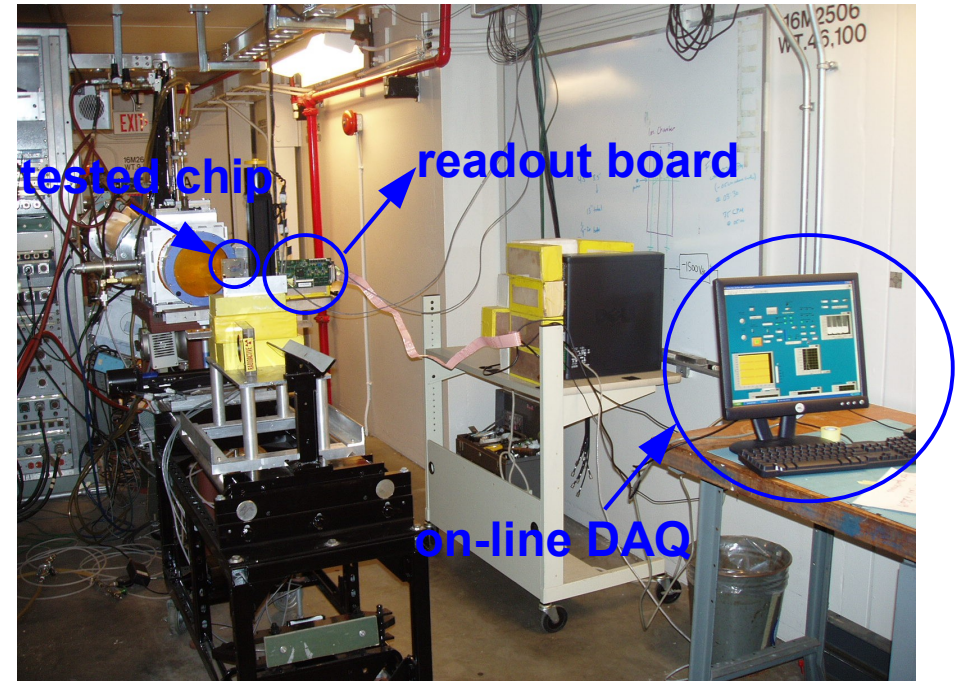
- Pixel scan with focused ($<10 \mu\text{m}$) 850 nm laser spot to study charge sharing
- Plot $\eta = \text{PH}_{\text{column}}^i / \text{PH}_{\text{cluster}}$ versus laser spot position
- From variation of signal fraction vs position along the pixels and S/N estimation of spatial resolution: $\sim 1.5\text{-}5 \mu\text{m}$ for 10-40 μm pitch pixels

850 nm Laser Scan, 40x40 μm^2 Pixels



Irradiations at the 88" Cyclotron

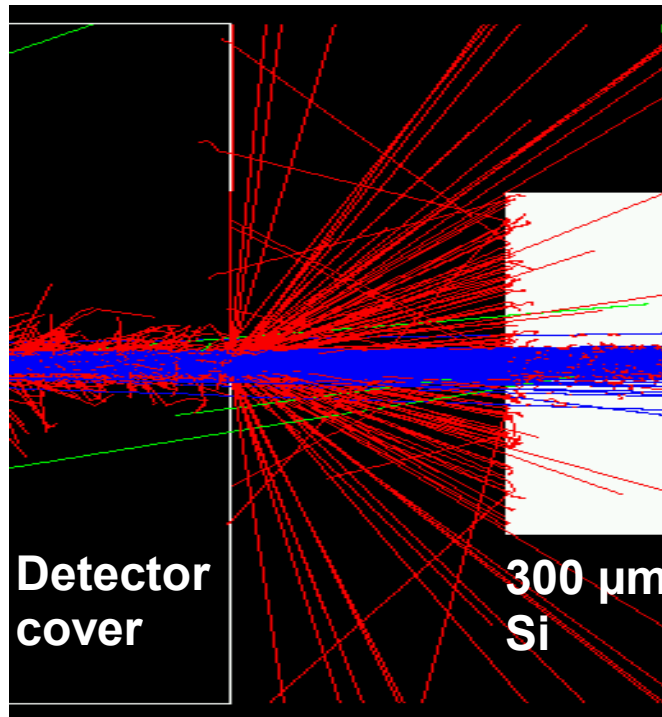
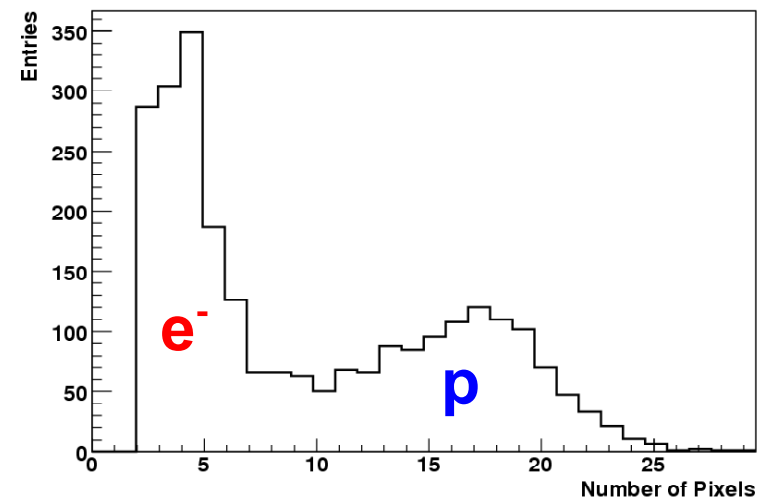
- Irradiation with 30 MeV protons up to 1.4×10^{12} p/cm²
- Proton flux $\sim 7 \times 10^7$ p/cm²/s
- Irradiation in steps: pedestal noise recorded after each step
- Low intensity beam runs in between different steps
- Detector powered on and kept in readout mode during irradiations



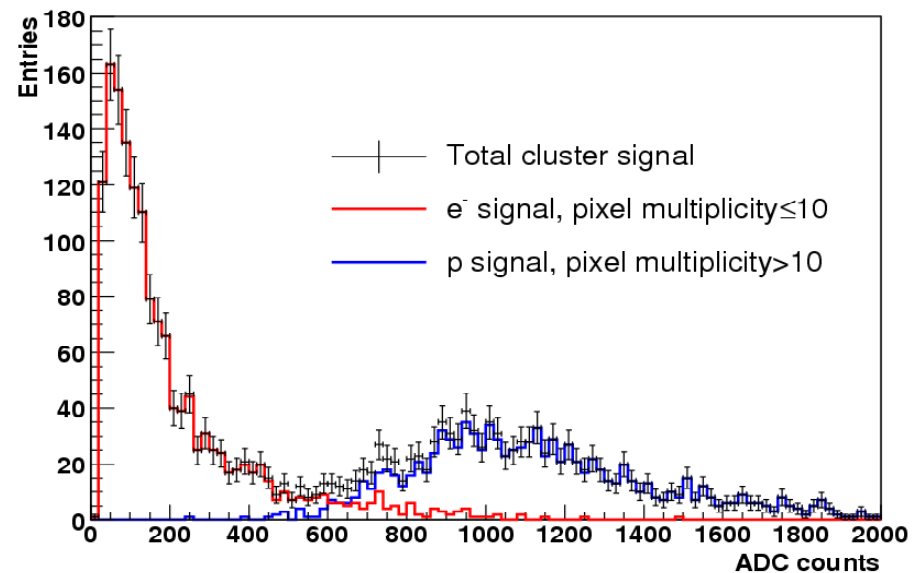
Test with 30 MeV proton beam

- Low intensity proton flux ($<2 \cdot 10^5$ p/cm²/s)
- Data acquired in free-running mode
- Double peak structure of pixel multiplicity distribution and correlated structure on cluster signal distribution
- Geant4 simulation: electrons produced by plastic detector cover

Pixel multiplicity, 30 MeV p beam

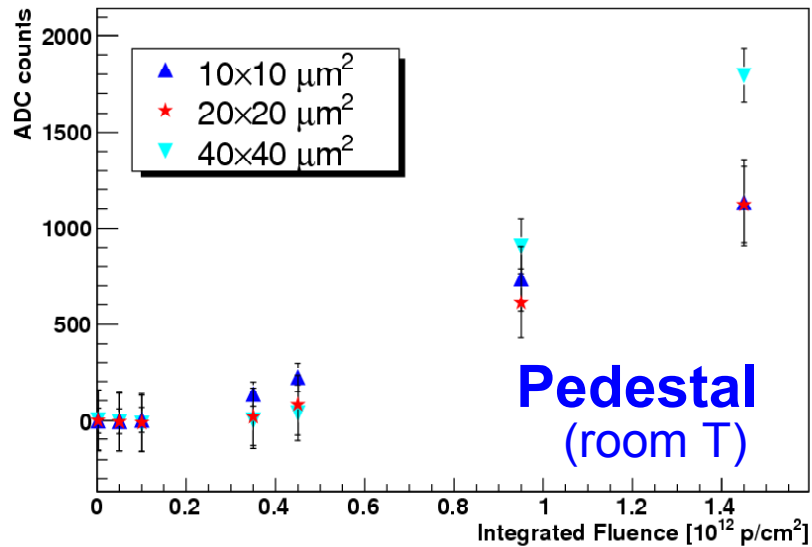


Cluster Signal, 30 MeV p beam

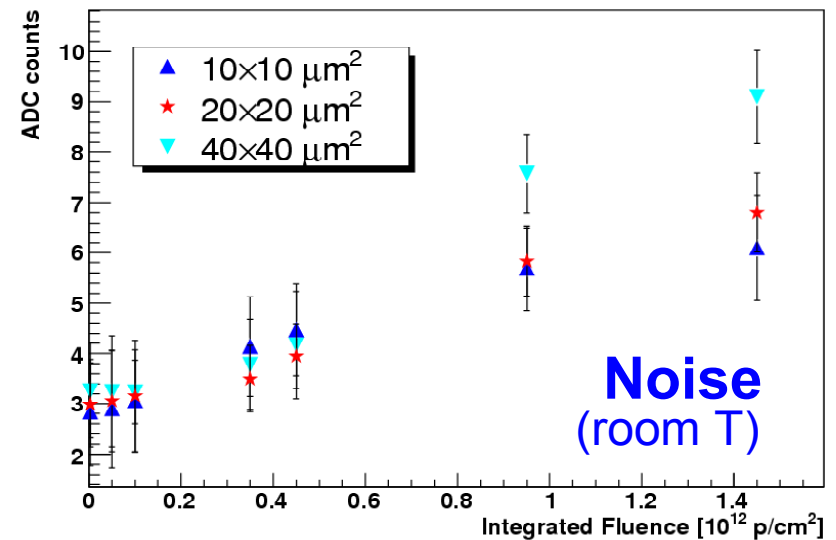


Test of irradiated prototype

Pedestal Variation vs Proton Fluence

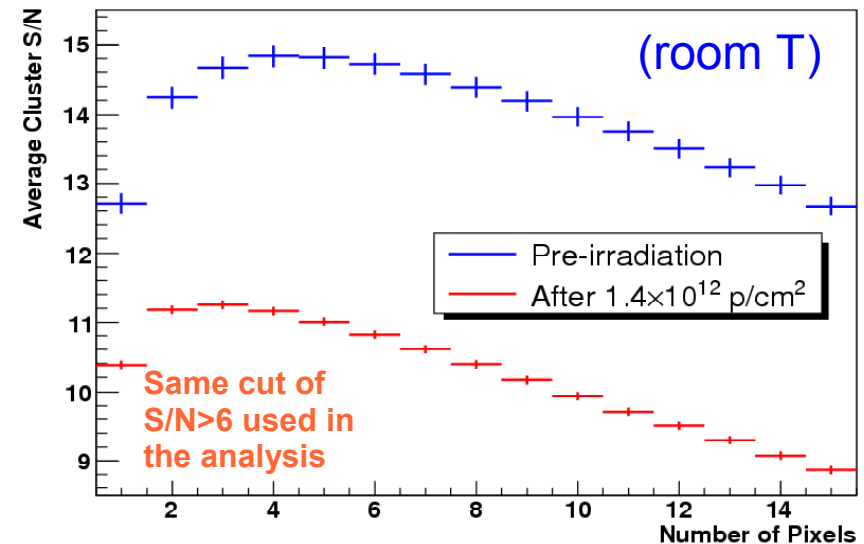


Average Noise vs Proton Fluence



- Linear increase of leakage current with fluence, more pronounced for larger pixels
- Better performance of smaller pixels
- Increase in noise correlated with increase in leakage current
- Corresponding degradation of S/N performance for mips, decrease of cluster multiplicity (trapping)
- Characterization of T dependence under way

Cluster S/N vs. Pixel Multiplicity



Back-thinning studies on MIMOSA-5

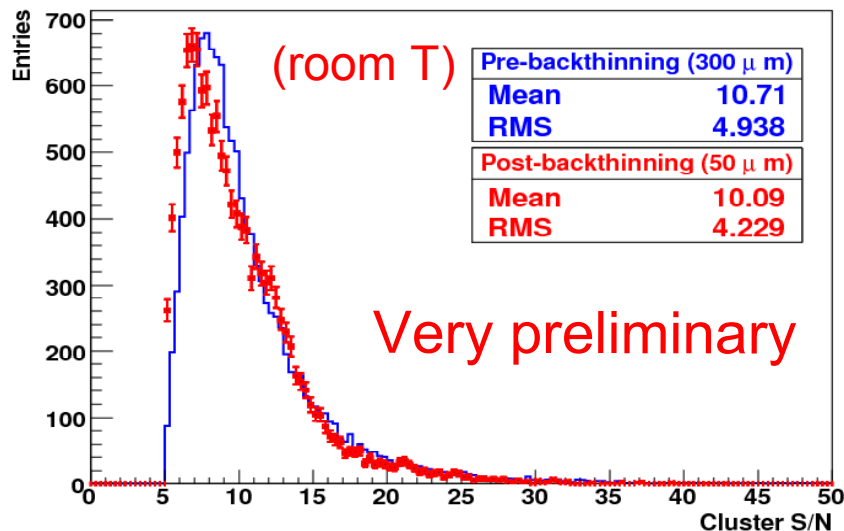


- Tests performed on diced MIMOSA-5 chips from IReS (Strasbourg)
- AMS 0.6 μm , 14 μm epilayer, 1 Mpixels on reticle-size area of $1.7 \times 1.9 \text{ cm}^2$, 17 μm pixel pitch

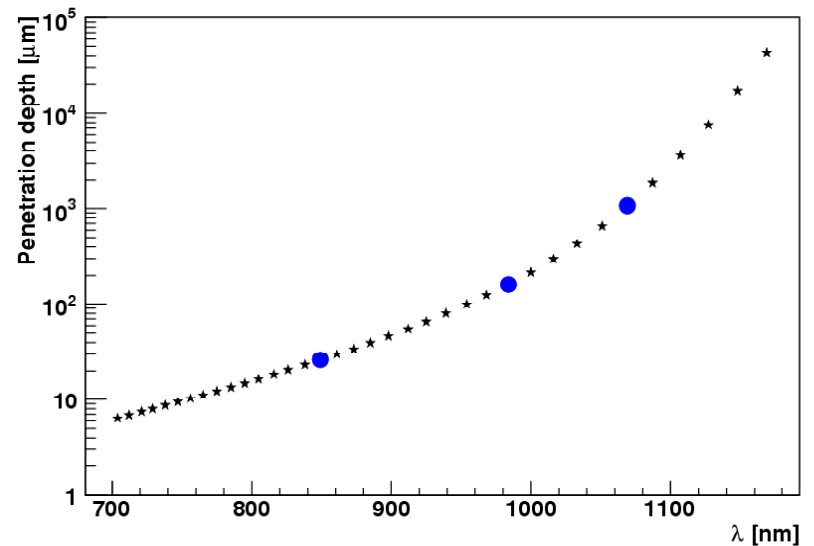
- Test with lasers of different wavelengths to probe signal from different silicon depths and estimate substrate contribution

- Back-thinning to 35-50 μm performed by Bay Area partner company

Cluster S/N comparison



Absorption of light in silicon



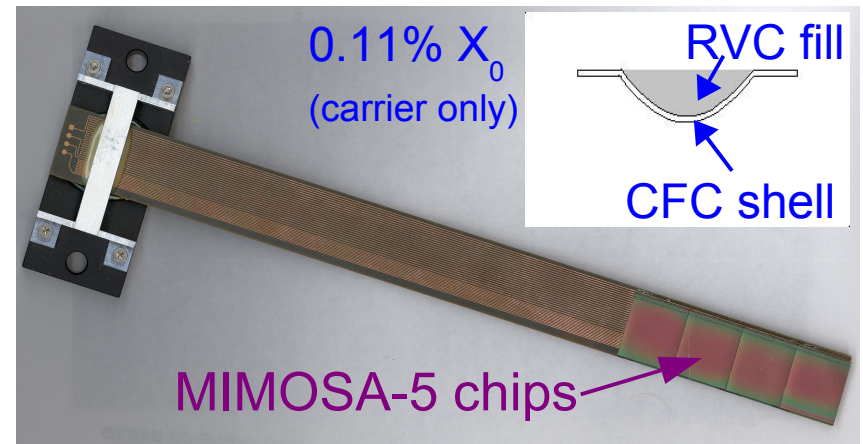
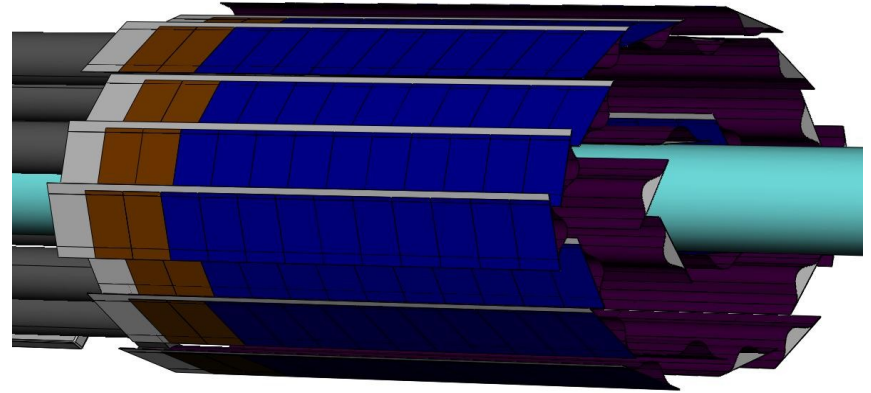
- Two chips back-thinned to 50 μm , tests under way with 1.5 GeV e^- and with lasers

- Very preliminary result from ALS beam-test (1.5 GeV e^-) @ room temperature

Pixel module engineering

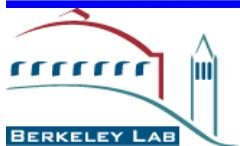
- Synergy with LBNL Nuclear Science Division, experience from the STAR HFT development
- Developed working ladder prototype with MIMOSA-5 chips back-thinned to 50 μm
- Important test of mechanical handling and assembly issues
- LCRD Proposal submitted for FY 2006-2007 for the design and development of a monolithic pixel detector module
 - optimization of sensor thickness
 - chip cooling requirements
 - design of low mass detector module
 - ladder integration and test under realistic operational conditions (e.g. power cycling)
- Leverage advantage of reduced material budget from thinner sensors with increased requirements on chip support structures

View of the STAR HFT

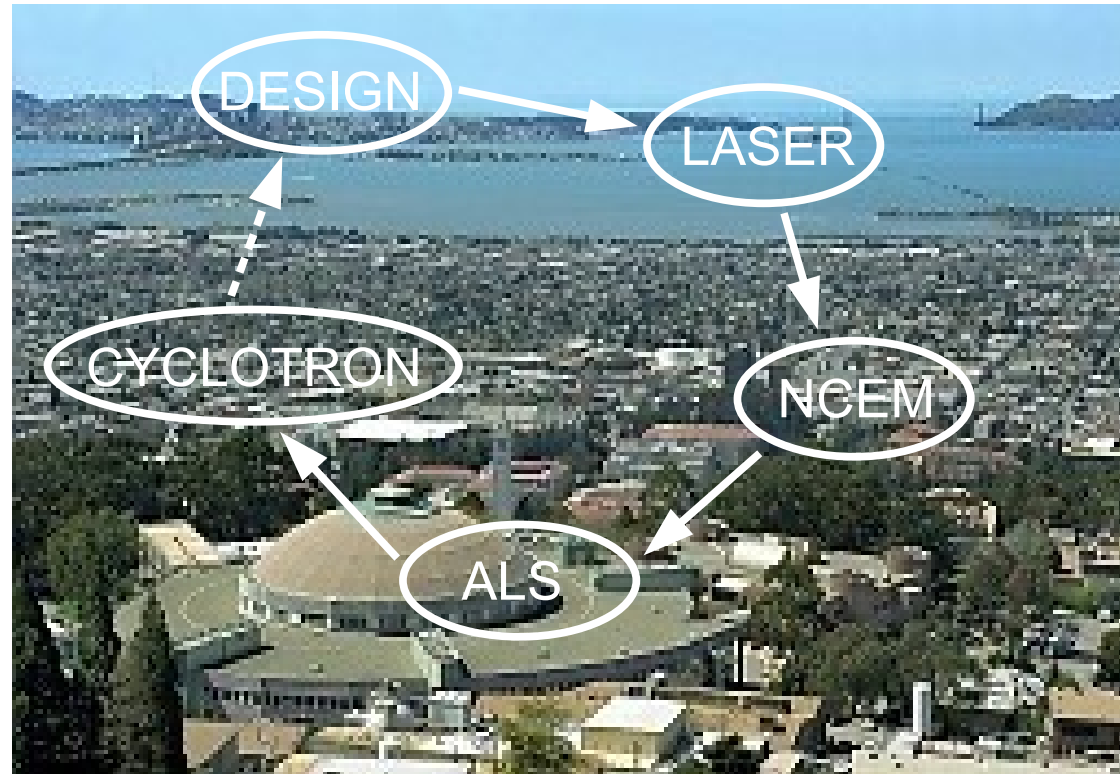


Outlook

- Pursue characterization of present prototype (T dependence), first **neutron irradiation** in April at the 88-inch Cyclotron
- **Next prototype submission through CMP in April**: various sub-matrices, different biasing schemes and diode sizes, on-pixel CDS
- Started design of **5-bit ADC with low power consumption** matching a 15 μm pixel pitch
→ **larger scale prototype including CP readout and on-chip ADC foreseen in early 2007**
- Extend **back-thinning studies on Mimosa-5 (down to 35 μm)** and forthcoming STAR prototypes
- **Deployed G4 Mokka full simulation and Marlin reconstruction framework at LBNL**: engaging in simulation studies including realistic digitization from beam-test cluster shapes, two cluster separation, study of machine-induced backgrounds (collaboration with AFRD), effect of geometry and ladder thickness on benchmark physics processes



Conclusions...



- LBNL ILC Pixels team has completed the first design-production-test cycle → next one to start over soon
- Present activities profit from collaborations with several institutes... more are welcome!